

PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

INJ0710AK1

High Speed Switching
Silicon P-channel MOSFET

DESCRIPTION

INJ0710AK1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery,
because of low voltage drive and low on resistance.

FEATURE

- Low on-resistance $R_{DS(ON)} = 27 \text{ m}\Omega$ (typ @ $V_{GS} = -10 \text{ V}$)
- High drain current $I_D = -7 \text{ A}$
- Drive voltage -4.0 V
- High speed switching.

APPLICATION

Switching Regulator, DC/DC Converter

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current(DC) (※1)	I_D	-7	A
Drain Current(Pulse) (※2)	I_{DP}	-20	A
Total Power Dissipation (※1)	P_D	2.5	W
Channel Temperature	T_{ch}	+150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

※1 package mounted on glass-epoxy substrate.

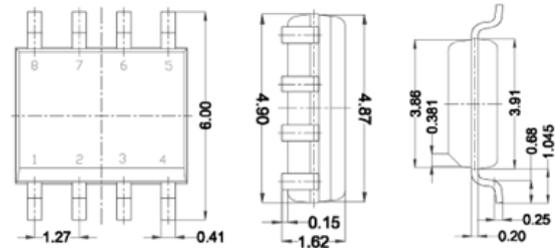
39mm × 39mm × 1.6mm

Copper foil with an area of 1460 mm² and a thickness of 35 μm

※2 : $P_w \leq 10 \text{ ms}$, Duty cycle $\leq 1\%$

OUTLINE DRAWING

Unit: mm

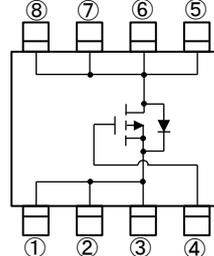


TERMINAL CONNECTOR

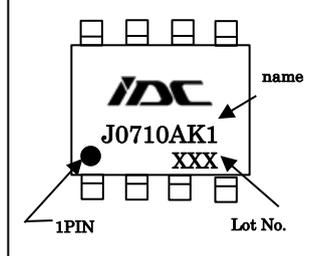
- ①: SOURCE
- ②: SOURCE
- ③: SOURCE
- ④: GATE
- ⑤: DRAIN
- ⑥: DRAIN
- ⑦: DRAIN
- ⑧: DRAIN

JEITA: SOP8

EQUIVALENT CIRCUIT



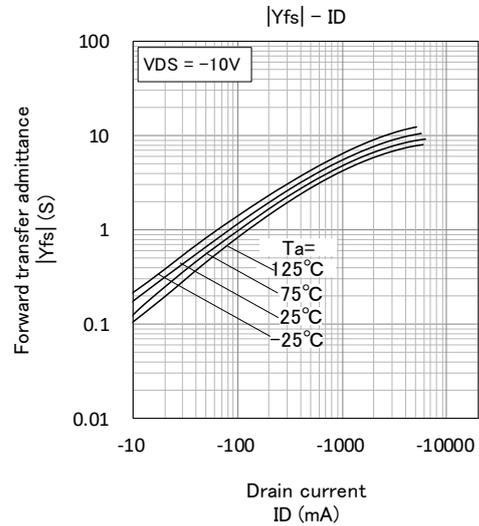
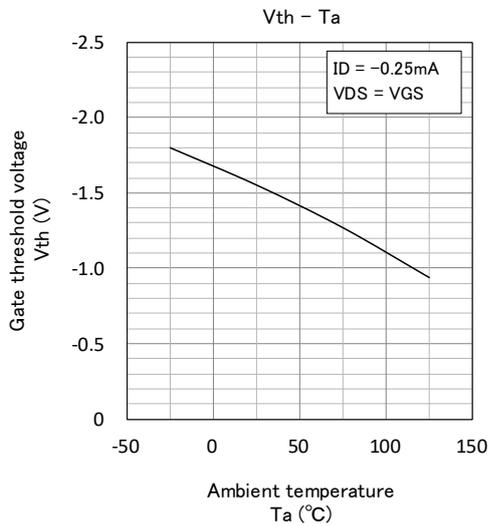
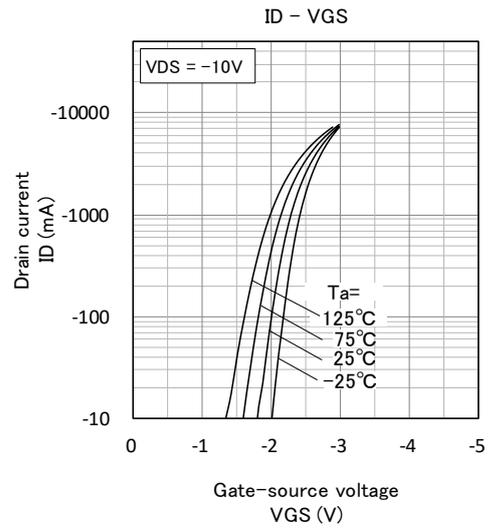
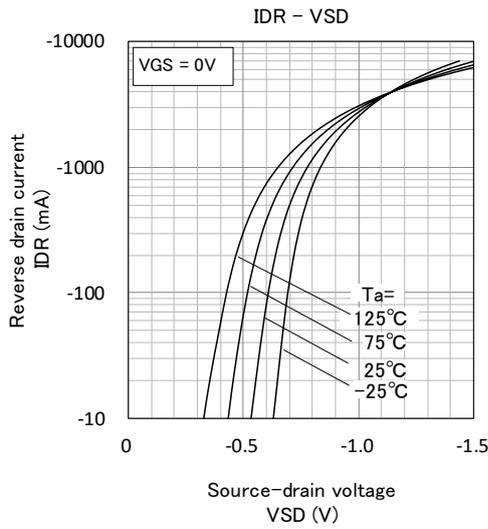
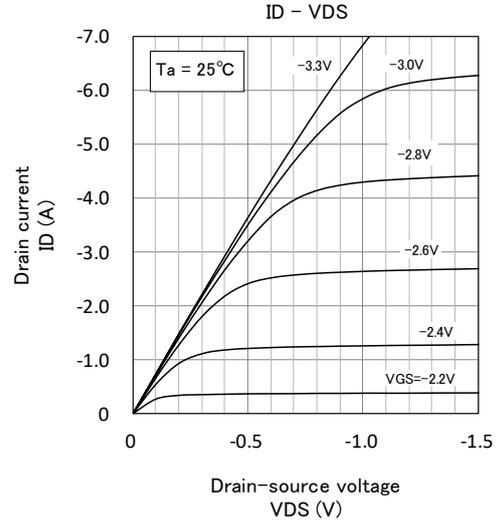
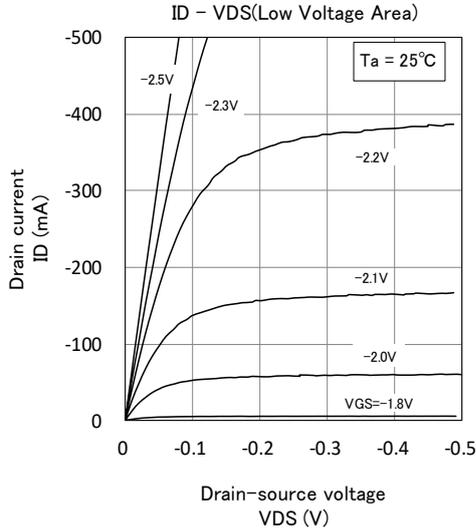
MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	-60	-	-	V
Gate-Source Leak Current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	± 0.1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	-1.0	μA
Gate Threshold Voltage	V_{th}	$I_D = -250 \mu\text{A}$, $V_{DS} = V_{GS}$	-1.0	-	-3.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = -7 \text{ A}$, $V_{GS} = -10 \text{ V}$	-	27	35	$\text{m}\Omega$
		$I_D = -5 \text{ A}$, $V_{GS} = -4.5 \text{ V}$	-	31	40	
Input Capacitance	C_{iss}	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	5700	-	pF
Output Capacitance	C_{oss}		-	340	-	
Feedback Capacitance	C_{rss}		-	240	-	
Switching Time	t_{on}	$V_{DS} = -20 \text{ V}$, $V_{GS} = -5 \text{ V}$,	-	110	-	ns
	T_{off}	$I_D = -200 \text{ mA}$,	-	300	-	

TYPICAL CHARACTERISTICS

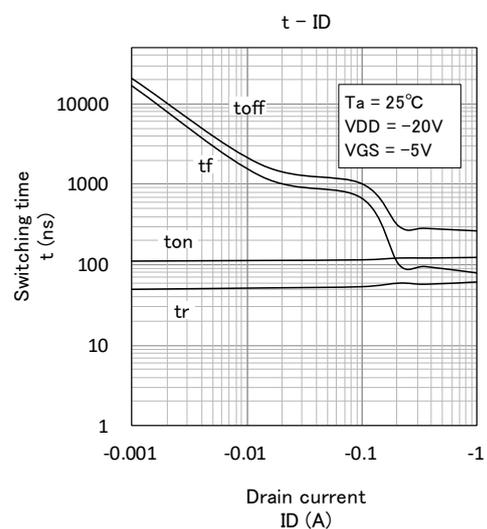
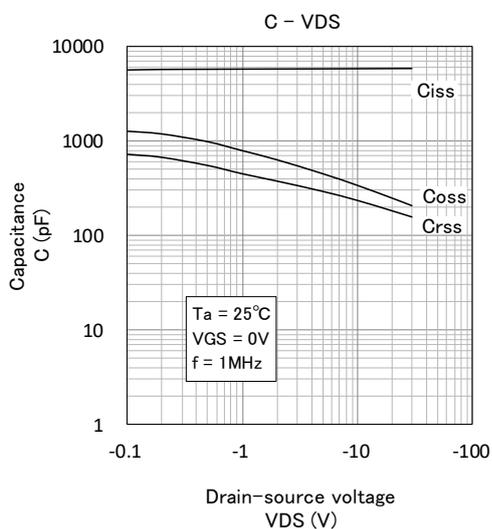
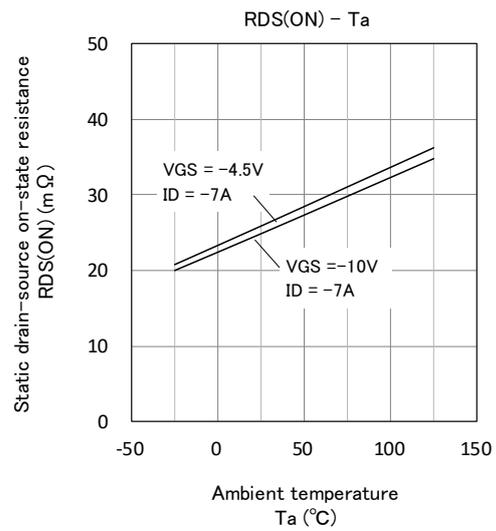
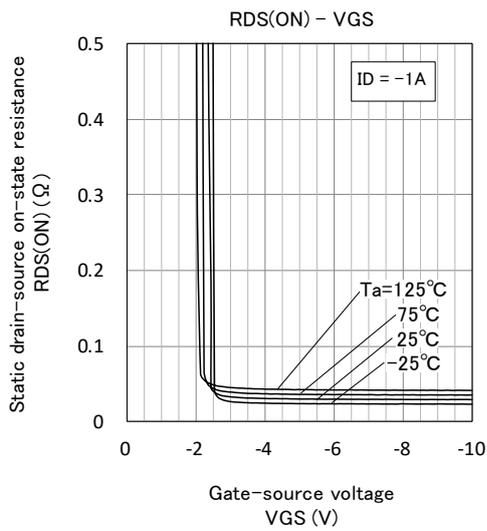
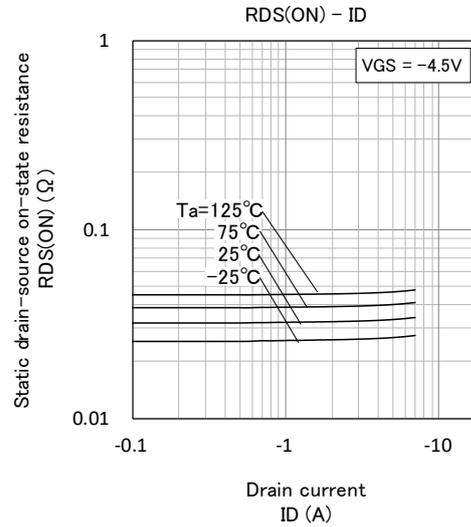
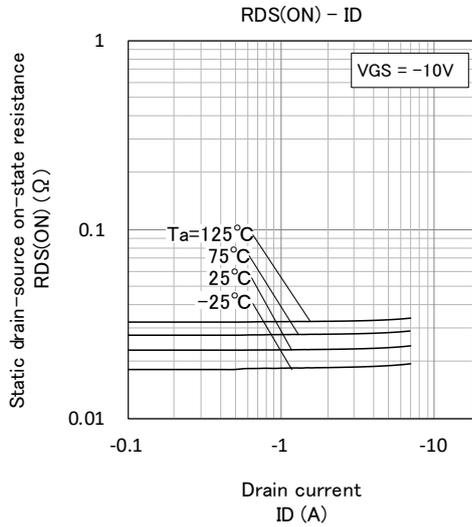


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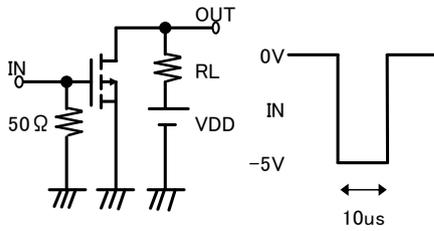
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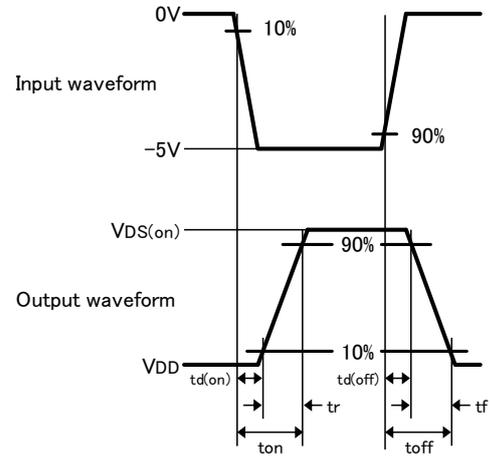
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Switching time test condition



Duty \leq 1%
Input: tr, tf < 10ns
VDD = -20V
Common source
Ta = 25°C



Keep safety first in your circuit designs!

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